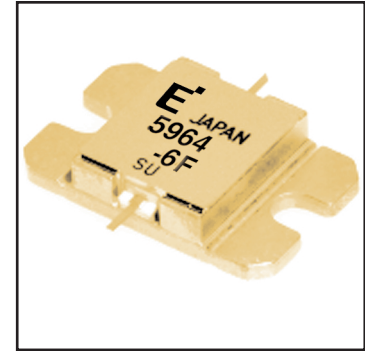


FEATURES

- High Output Power: $P_{1dB} = 38.5dBm$ (Typ.)
- High Gain: $G_{1dB} = 10.0dB$ (Typ.)
- High PAE: $\eta_{add} = 37%$ (Typ.)
- Low $IM_3 = -46dBc @ P_o = 27.5dBm$
- Broad Band: 5.9 ~ 6.4GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package



DESCRIPTION

The FLM5964-6F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ C$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_C = 25^\circ C$	31.2	W
Storage Temperature	T_{stg}		-65 to +175	$^\circ C$
Channel Temperature	T_{ch}		175	$^\circ C$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 16.0 and -2.8 mA respectively with gate resistance of 100 Ω .

ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ C$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS} = 5V, V_{GS} = 0V$	-	2500	3750	mA
Transconductance	g_m	$V_{DS} = 5V, I_{DS} = 1625mA$	-	2500	-	mS
Pinch-off Voltage	V_p	$V_{DS} = 5V, I_{DS} = 125mA$	-0.5	-1.5	-3.0	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS} = -125\mu A$	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS} = 10V,$ $I_{DS} = 0.65I_{DSS}$ (Typ.), $f = 5.9 \sim 6.4$ GHz, $Z_S = Z_L = 50$ ohm	37.5	38.5	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		9.0	10.0	-	dB
Drain Current	I_{dsr}		-	1625	1900	mA
Power-added Efficiency	η_{add}		-	37	-	%
Gain Flatness	ΔG		-	-	± 0.6	dB
3rd Order Intermodulation Distortion	IM_3	$f = 6.4$ GHz, $\Delta f = 10$ MHz 2-Tone Test $P_{out} = 27.5dBm$ S.C.L.	-44	-46	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	4.0	4.8	$^\circ C/W$
Channel Temperature Rise	ΔT_{ch}	$10V \times I_{dsr} \times R_{th}$	-	-	80	$^\circ C$

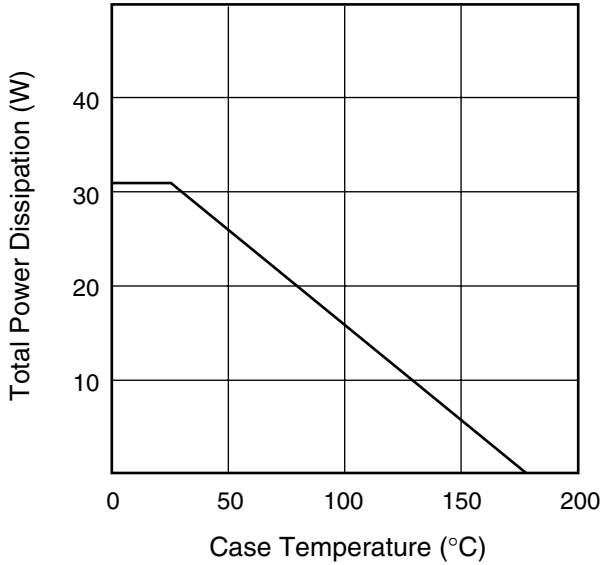
CASE STYLE: IB

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

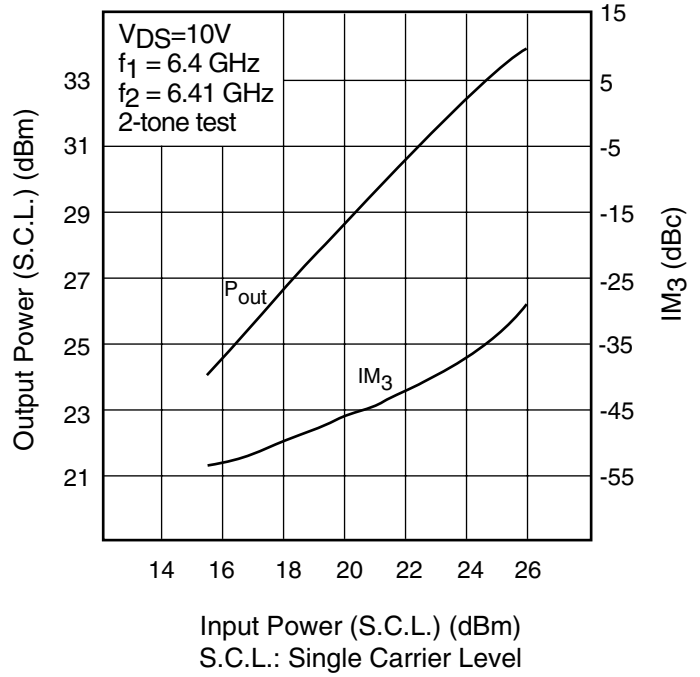
FLM5964-6F

C-Band Internally Matched FET

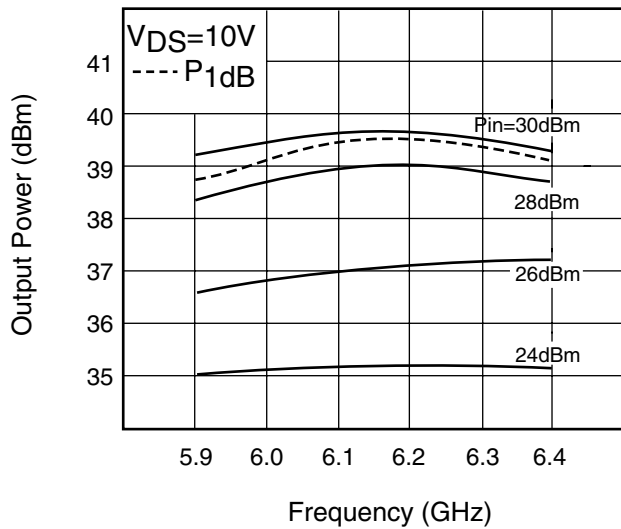
POWER DERATING CURVE



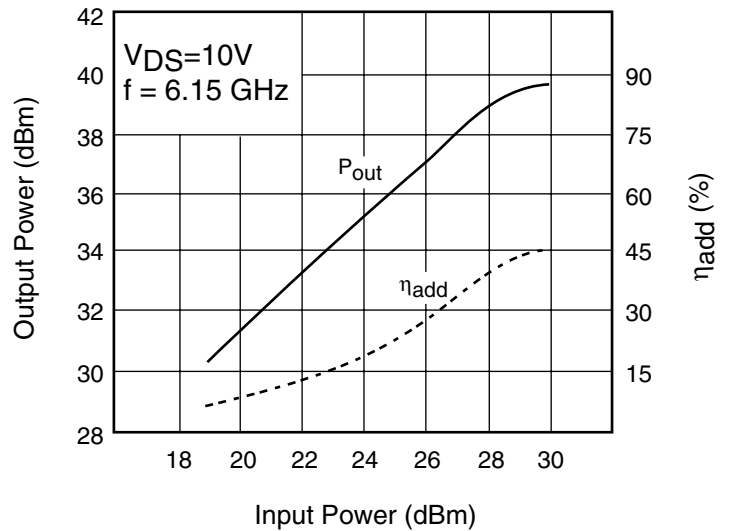
OUTPUT POWER & IM₃ vs. INPUT POWER

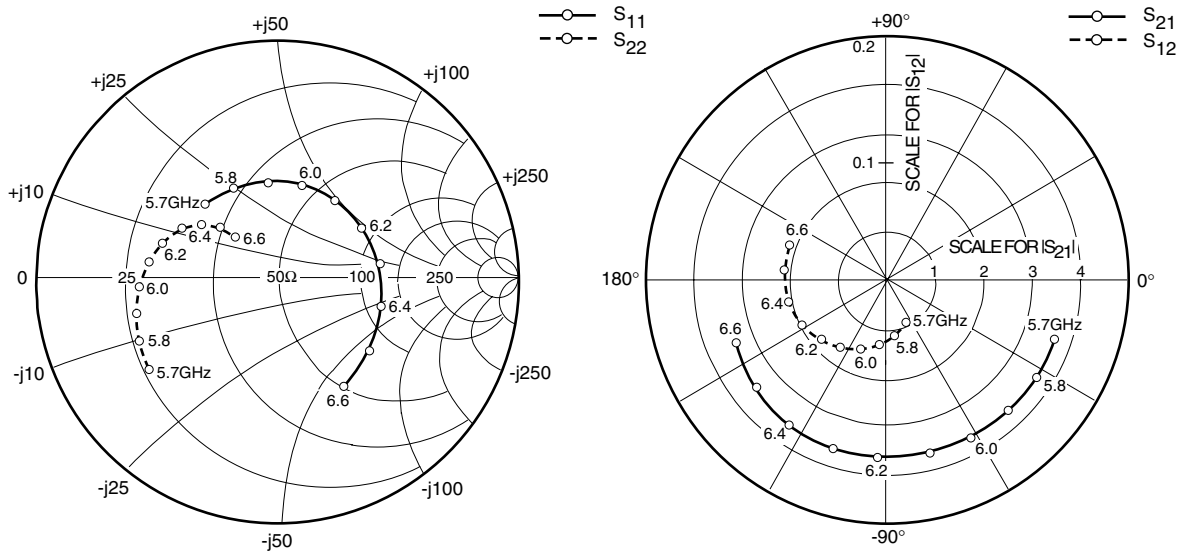


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER





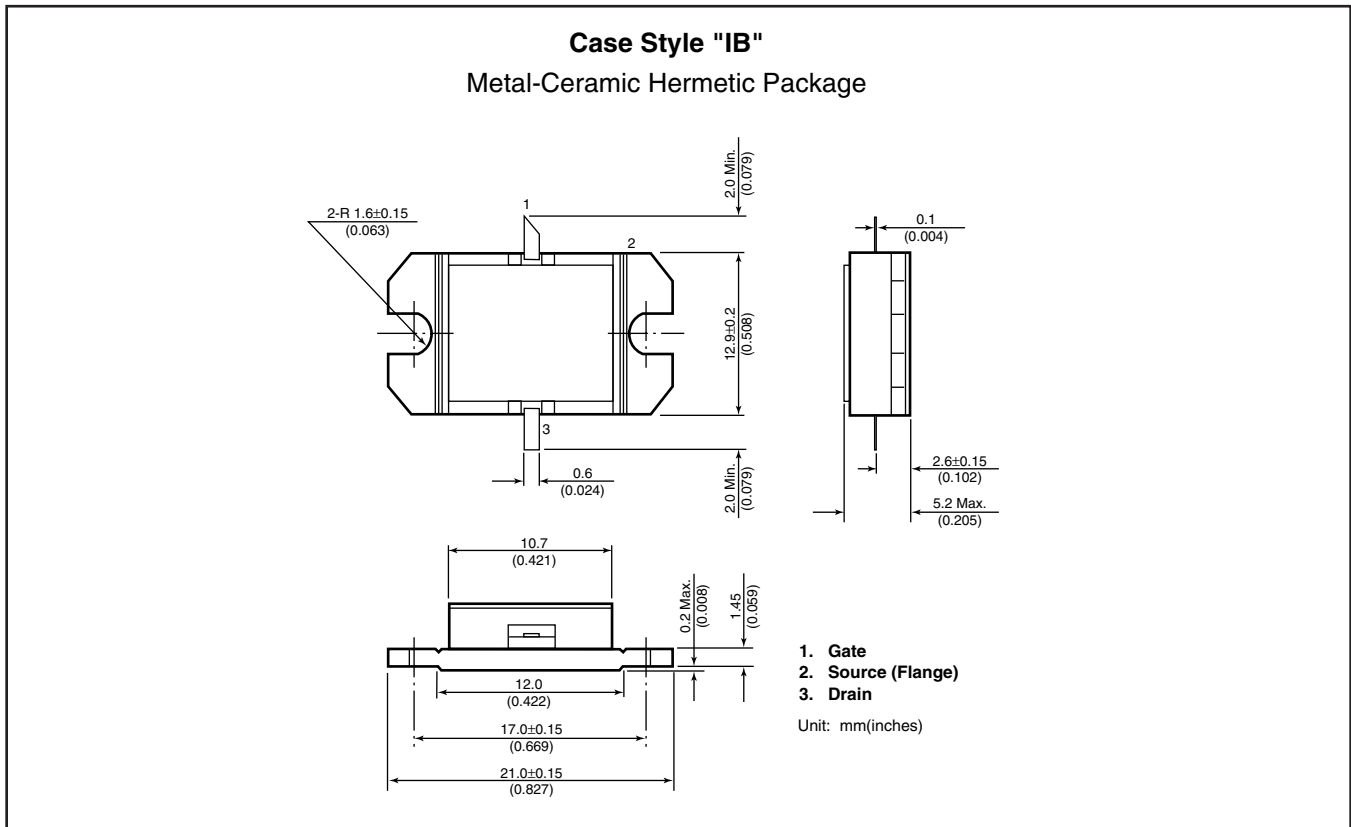
S-PARAMETERS

$V_{DS} = 10V, I_{DS} = 1625mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
5700	.432	134.8	3.652	-19.7	.037	-65.3	.660	-145.4
5800	.417	116.5	3.676	-33.5	.045	-83.1	.641	-156.0
5900	.403	97.1	3.681	-47.6	.053	-98.2	.617	-166.4
6000	.395	75.9	3.705	-62.1	.061	-112.7	.589	-176.7
6100	.391	53.8	3.708	-77.0	.068	-126.4	.555	173.0
6200	.398	30.4	3.696	-92.2	.074	-140.2	.512	163.0
6300	.416	7.1	3.661	-107.9	.079	-154.4	.458	153.7
6400	.446	-16.1	3.609	-123.9	.083	-169.3	.396	145.0
6500	.484	-38.9	3.525	-140.6	.085	175.5	.325	138.7
6600	.529	-60.1	3.399	-157.1	.086	160.2	.253	137.3

FLM5964-6F

C-Band Internally Matched FET



For further information please contact:

Eudyna Devices USA Inc.

2355 Zanker Rd.
San Jose, CA 95131-1138, U.S.A.
TEL: (408) 232-9500
FAX: (408) 428-9111
www.us.eudyna.com

Eudyna Devices Europe Ltd.

Network House
Norreys Drive
Maidenhead, Berkshire SL6 4FJ
United Kingdom
TEL: +44 (0) 1628 504800
FAX: +44 (0) 1628 504888

Eudyna Devices Asia Pte Ltd.

Hong Kong Branch
Rm. 1101, Ocean Centre, 5 Canton Rd.
Tsim Sha Tsui, Kowloon, Hong Kong
TEL: +852-2377-0227
FAX: +852-2377-3921

Eudyna Devices Inc.

Sales Division
1, Kanai-cho, Sakae-ku
Yokohama, 244-0845, Japan
TEL: +81-45-853-8156
FAX: +81-45-853-8170

CAUTION

Eudyna Devices Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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